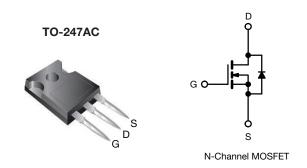
Vishay Siliconix

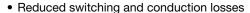
## **Power MOSFET**



PRODUCT SUMMARY				
V <sub>DS</sub> (V) at T <sub>J</sub> max. 550				
R <sub>DS(on)</sub> typ. (Ω) at 25 °C	V <sub>GS</sub> = 10 V	0.234		
Q <sub>g</sub> max. (nC)	116			
Q <sub>gs</sub> (nC)	22			
Q <sub>gd</sub> (nC)	35			
Configuration	Single			

### **FEATURES**

- Low figure-of-merit (FOM) Ron x Qa
- Low effective capacitance (Co(er))



Avalanche energy rated (UIS)

• Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

# COMPLIANT HALOGEN **FREE**

### **APPLICATIONS**

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Solar (PV inverters)

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and halogen-free	IRFP460HPBF

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			$V_{DS}$	500	V
Gate-source voltage			$V_{GS}$	± 30	v
Continuous drain surrent (T = 150 °C)	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C T <sub>C</sub> = 100 °C	1	20	
Continuous drain current ( $T_J = 150 ^{\circ}\text{C}$ ) $V_{GS}$ at 10 V $T_{C} = 10$		T <sub>C</sub> = 100 °C	I <sub>D</sub>	13	Α
Pulsed drain current <sup>a</sup>			I <sub>DM</sub>	54	
Linear derating factor				2.6	W/°C
Single pulse avalanche energy b			E <sub>AS</sub>	621	mJ
Maximum power dissipation			$P_{D}$	329	W
Operating junction and storage temperature range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Drain-source voltage slope $T_J = 125 ^{\circ}\text{C}$		dy (/dł	66	V/ns	
Reverse diode dv/dt d			dv/dt	0.5	V/ns
Soldering recommendations (peak temperature)	For	10 s		260	°C

- a. Repetitive rating; pulse width limited by maximum junction temperature
- b.  $V_{DD}$  = 120 V, starting  $T_J$  = 25 °C, L = 4.3 mH,  $R_q$  = 25  $\Omega$ ,  $I_{AS}$  = 17 A
- c. 1.6 mm from case
- d.  $I_{SD} \le I_D$ , di/dt = 100 A/ $\mu$ s, starting  $T_J = 25$  °C



# Vishay Siliconix

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R <sub>thJA</sub>	-	40	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	0.45	C/VV

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		500	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	Referenc	e to 25 °C, I <sub>D</sub> = 1 mA	-	0.56	-	V/°C
Gate-source threshold voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	-	4.0	V
Oala a sana lada a sa		,	$V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
Gate-source leakage	I <sub>GSS</sub>	,	$V_{GS} = \pm 30 \text{ V}$	-	-	± 1	μA
Zana mata waltana alusia awanat		V <sub>DS</sub> =	500 V, V <sub>GS</sub> = 0 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 400 V	, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	100	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 12 A	-	0.234	0.270	Ω
Forward transconductance a	9 <sub>fs</sub>	V <sub>DS</sub>	= 10 V, I <sub>D</sub> = 12 A	-	9.6	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>		V <sub>GS</sub> = 0 V,	-	3208	-	
Output capacitance	C <sub>oss</sub>	,	$V_{DS} = 100 \text{ V},$	-	163	-	-
Reverse transfer capacitance	C <sub>rss</sub>		f = 1 MHz		17	-	pF
Effective output capacitance, energy related <sup>a</sup>	C <sub>o(er)</sub>			-	114	-	
Effective output capacitance, time related <sup>b</sup>	C <sub>o(tr)</sub>	V <sub>DS</sub> = 0 \	$V_{DS} = 0 \text{ V to } 480 \text{ V}, V_{GS} = 0 \text{ V}$		206	-	
Total gate charge	Qg			-	77	116	
Gate-source charge	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$I_D = 12 \text{ A}, V_{DS} = 400 \text{ V}$	-	22	-	nC
Gate-drain charge	Q <sub>gd</sub>			-	35	-	
Turn-on delay time	t <sub>d(on)</sub>			-	29	58	
Rise time	t <sub>r</sub>	$V_{DD} =$	400 V, I <sub>D</sub> = 12 A,	-	60	90	
Turn-off delay time	t <sub>d(off)</sub>	V <sub>GS</sub> =	$= 10 \text{ V}, \text{ R}_{\text{g}} = 9.1 \Omega$	-	67	101	ns
Fall time	t <sub>f</sub>			-	47	94	
Gate input resistance	$R_g$	f = 1	MHz, open drain	0.37	0.75	1.5	Ω
Drain-Source Body Diode Characteristic	s						
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	22	
Pulsed diode forward current	I <sub>SM</sub>			-	-	54	A
Diode forward voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C	C, I <sub>S</sub> = 12 A, V <sub>GS</sub> = 0 V	-	-	1.2	V
Reverse recovery time	t <sub>rr</sub>			-	384	768	ns
Reverse recovery charge	Q <sub>rr</sub>	$T_J = 25$	5 °C, I <sub>F</sub> = I <sub>S</sub> = 12 A,	-	5.1	10.2	μC
Reverse recovery current	I <sub>RRM</sub>	$di/dt = 100 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 25 \text{ V}$		-	26	_	A



### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

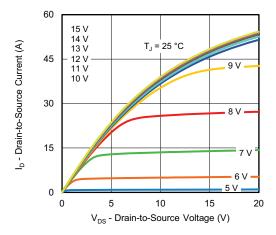


Fig. 1 - Typical Output Characteristics

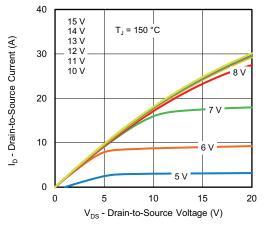


Fig. 2 - Typical Output Characteristics

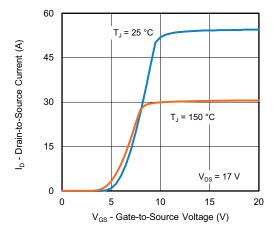


Fig. 3 - Typical Transfer Characteristics

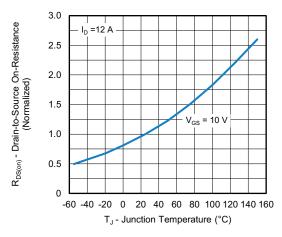


Fig. 4 - Normalized On-Resistance vs. Temperature

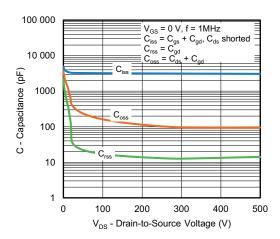


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

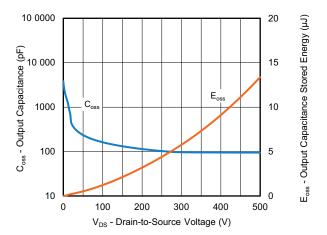


Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$ 



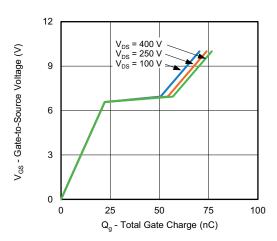


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

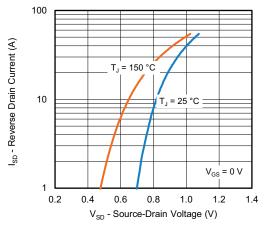


Fig. 8 - Typical Source-Drain Diode Forward Voltage

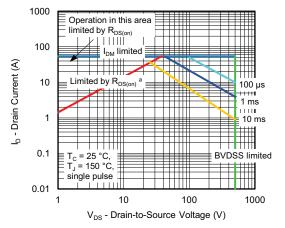


Fig. 9 - Maximum Safe Operating Area

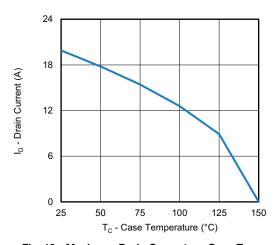


Fig. 10 - Maximum Drain Current vs. Case Temperature

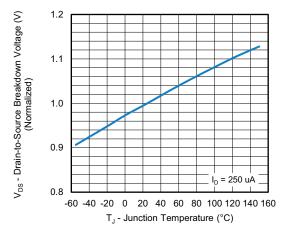


Fig. 11 - Temperature vs. Drain-to-Source Voltage



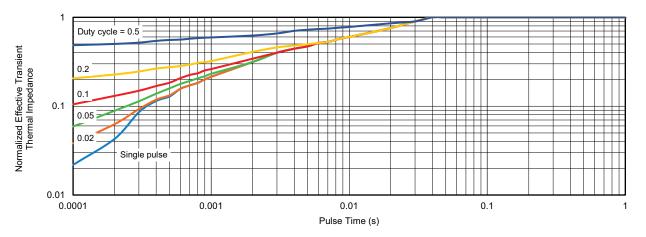


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

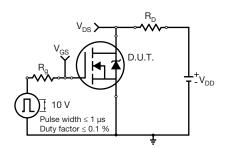


Fig. 13 - Switching Time Test Circuit

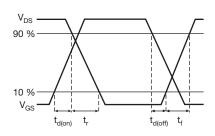


Fig. 14 - Switching Time Waveforms

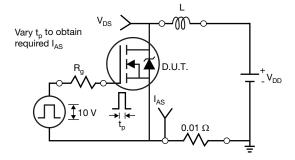


Fig. 15 - Unclamped Inductive Test Circuit

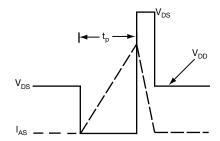


Fig. 16 - Unclamped Inductive Waveforms

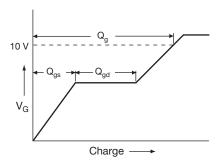


Fig. 17 - Basic Gate Charge Waveform

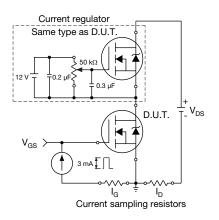
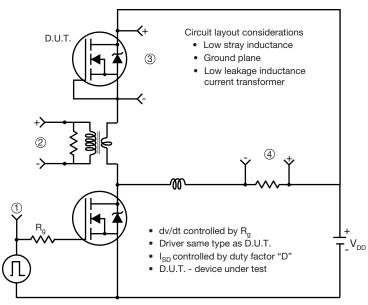




Fig. 18 - Gate Charge Test Circuit

### Peak Diode Recovery dv/dt Test Circuit



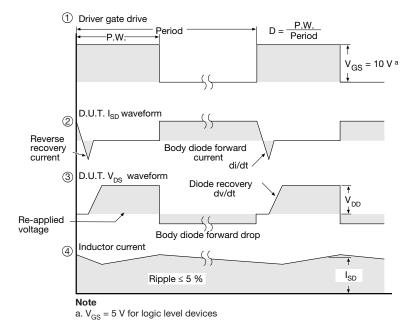


Fig. 19 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon

### IRFP460HPBF



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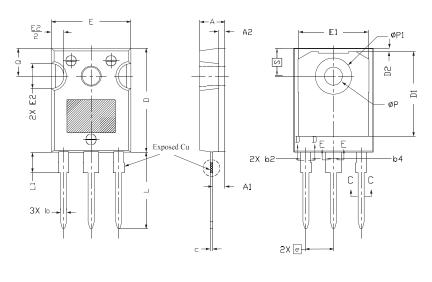
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Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?92440">www.vishay.com/ppg?92440</a>.



# **TO-247AC (High Voltage)**

### **VERSION 1: FACILITY CODE = 9**







Section C--C,D-D,E-E

	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES	
Α	4.83	5.02	5.21		
A1	2.29	2.41	2.55		
A2	1.17	1.27	1.37		
b	1.12	1.20	1.33		
b1	1.12	1.20	1.28		
b2	1.91	2.00	2.39	6	
b3	1.91	2.00	2.34		
b4	2.87	3.00	3.22	6, 8	
b5	2.87	3.00	3.18		
С	0.40	0.50	0.60	6	
c1	0.40	0.50	0.56		
D	20.40	20.55	20.70	4	

	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
Е	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е				
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØΡ	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

#### Notes

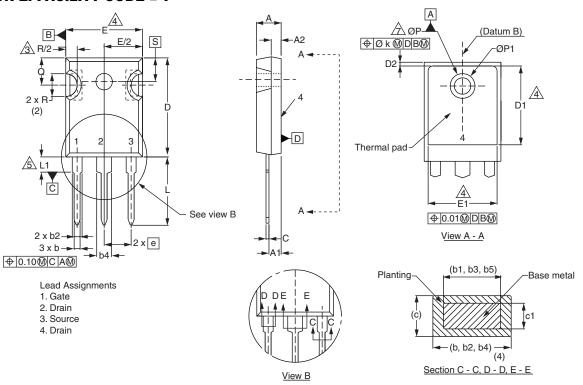
- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$  Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



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### **VERSION 2: FACILITY CODE = Y**



	MILLIM		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
Е	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

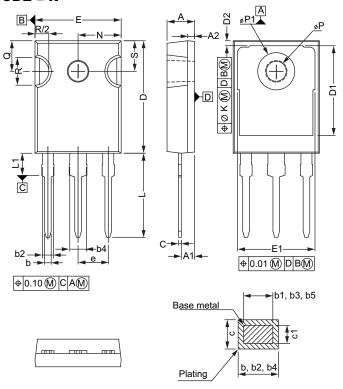
#### **Notes**

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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### **VERSION 3: FACILITY CODE = N**



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

### **Notes**

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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